

Power Matters."

Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$; $V_{CE} = 1200V$				250	μA
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	1.4	1.7	2.1	V
V _{CE(sat)}		$I_C = 50A$	$T_{j} = 125^{\circ}C$		2.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C _{ies}	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$			3600		pF
C _{rss}	Reverse Transfer Capacitance	f=1MHz		160		P1	
Q_{G}	Gate charge	$V_{GE}=\pm 15V, I_C=50A$ $V_{CE}=600V$			0.47		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 50A$			90		
Tr	Rise Time				30		ns
T _{d(off)}	Turn-off Delay Time				420		
T_{f}	Fall Time	$R_G = 18\Omega$		70			
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 50A$			90		
Tr	Rise Time				50		
T _{d(off)}	Turn-off Delay Time				520		ns
$T_{\rm f}$	Fall Time	$R_G = 18\Omega$	C		90		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125^{\circ}C$		5		
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$I_{\rm C} = 50 A$ $R_{\rm G} = 18 \Omega$	$T_j = 125^{\circ}C$		5.5		mJ
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 900V$ $t_p \le 10\mu s$; $T_j = 125^{\circ}C$			200		Α
R _{thJC}	Junction to Case Thermal Resistance					0.45	°C/W

Chopper diode ratings and characteristics (Per diode)

			Min	Тур	Max	Unit
Peak Repetitive Reverse Voltage					1200	V
Reverse Leakage Current	V _R =1200V				250	μA
DC Forward Current		$Tc = 70^{\circ}C$		60		А
Diode Forward Voltage	$I_F = 60A$			2	2.5	
	$I_F = 120A$			2.3		V
	$I_F = 60A$	$T_{j} = 125^{\circ}C$		1.8		
Reverse Recovery Time	$I_{\rm F} = 60 \text{A}$ $V_{\rm R} = 800 \text{V}$ $di/dt = 200 \text{A}/\mu \text{s}$	$T_j = 25^{\circ}C$		400		ns
		$T_{j} = 125^{\circ}C$		470		115
Reverse Recovery Charge		$T_j = 25^{\circ}C$		1200	n	nC
		$T_{j} = 125^{\circ}C$		4000		ne
Reverse Recovery Energy	$I_F = 60A$ $V_R = 800V$ $di/dt = 1000A/\mu s$	$T_j = 125^{\circ}C$		2.2		mJ
Junction to Case Thermal Resistance					0.9	°C/W
	DC Forward Current Diode Forward Voltage Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Energy	$ \begin{array}{c} DC \ Forward \ Current \\ \hline Diode \ Forward \ Voltage \\ \hline I_F = 60A \\ \hline I_F = 60A \\ \hline I_F = 60A \\ \hline V_R = 800V \\ \hline di/dt = 200A/\mu s \\ \hline Reverse \ Recovery \ Energy \\ \hline I_F = 60A \\ \hline V_R = 800V \\ \hline di/dt = 1000A/\mu s \\ \hline \end{array} $	$ \begin{array}{c c} DC \ Forward \ Current \\ \hline DC \ Forward \ Current \\ \hline Diode \ Forward \ Voltage \\ \hline I_F = 60 A \\ \hline I_F = 120 A \\ \hline I_F = 120 A \\ \hline I_F = 60 A \\ \hline V_R = 800 V \\ di/dt = 200 A/\mu s \\ \hline T_j = 125^\circ C \\ \hline $	DC Forward Current $Tc = 70^{\circ}C$ Diode Forward Voltage $I_F = 60A$ $I_F = 120A$ $I_F = 60A$ $T_j = 125^{\circ}C$ $T_j = 25^{\circ}C$ Reverse Recovery Time $I_F = 60A$ $T_j = 25^{\circ}C$ Reverse Recovery Charge $U_R = 800V$ $T_j = 25^{\circ}C$ Reverse Recovery Energy $I_F = 60A$ $T_j = 125^{\circ}C$ $I_F = 60A$ $T_j = 125^{\circ}C$ $I_F = 60A$ $V_R = 800V$ $T_j = 125^{\circ}C$	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $

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Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

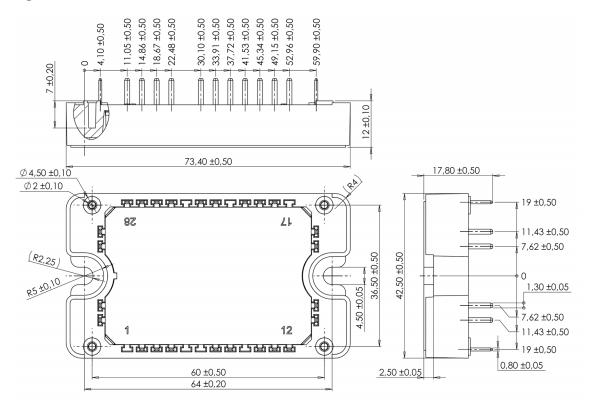
Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		Κ
$\Delta B/B$		T _C =100°C		4		%
	D					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$ T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T _J	Operating junction temperature range			-40	175	
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T _{STG}	Storage Temperature Range			-40	125	C
T _C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Package outline (dimensions in mm)

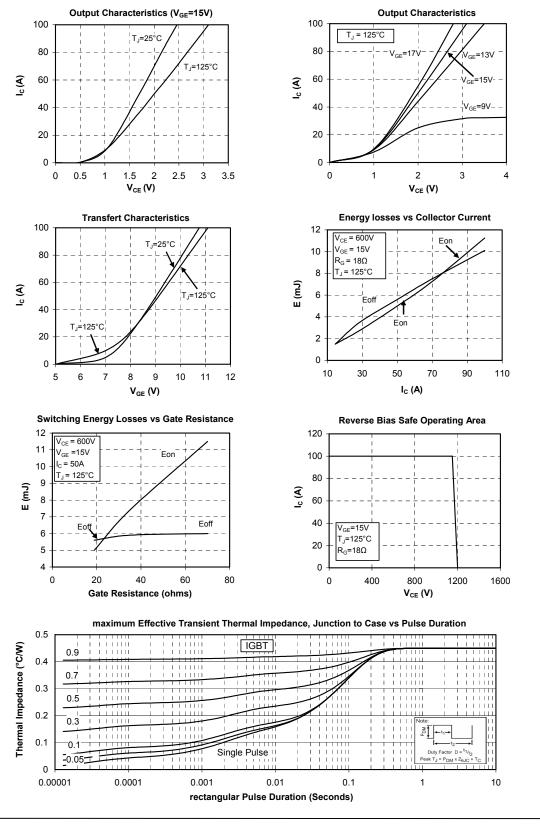


See application note - 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

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Typical Performance Curve

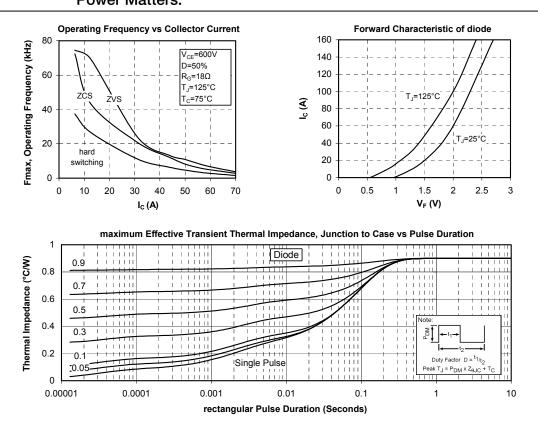


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